

Section I. (Amendment to the Claims)

Following is a listing of claims 1-33 as amended herein, with markings to show changes made:

1. (Currently amended) A method for forming a low resistance MOSFET device comprising ~~the steps of:~~
 - forming a gate region atop a surface of a substrate;
 - forming first spacers each having a first spacer width on sidewalls of said gate region;
 - forming a dopant region comprising source/drain extensions and deep source/drain regions in said substrate using a single dopant implant step;
 - forming first silicide regions each having a first vertical silicide thickness in said substrate ~~as well as atop a surface of said gate region, wherein said first silicide regions have a lateral thickness from about 2 to about 15 nm which lowers external resistance of said device;~~
 - forming second spacers ~~in atop said substrate and atop a surface of said gate region~~ each having a second spacer width along sidewalls of the first spacers, wherein said second spacers protect said first silicide regions in said substrate; and
 - forming second silicide regions in said substrate ~~and atop a surface of said gate region,~~ wherein said second silicide regions each have a second vertical silicide thickness that is greater than said first vertical silicide thickness, and wherein the first vertical silicide thickness is from about 2 to about 15 nm.
2. (Original) The method of Claim 1 wherein said forming of said gate region further comprises predoping of said gate region.
3. (Original) The method of Claim 2 wherein said predoping is performed by ion implantation of a type III-A element or a type V element into said gate region.

4. (Original) The method of Claim 3 where predoping is achieved via ion implantation of phosphorus into said gate region.
5. (Cancelled)
6. (Previously presented) The method of Claim 1 wherein said first spacers width is from about 5 nm to about 20 nm.
7. (Previously presented) The method of Claim 1 wherein said first spacers width is from about 7 nm to about 15 nm.
8. (Original) The method of Claim 1 wherein said second spacers width is from about 20 nm to about 90 nm.
9. (Original) The method of Claim 1 wherein said second spacers width is from about 30 nm to about 70 nm.
- 10-11. (Cancelled)
12. (Presently presented) The method of Claim 1 wherein said forming of said first silicide regions comprises depositing a first metal layer upon an exposed surface of said substrate and annealing.
13. (Original) The method of Claim 12 where said first metal layer has a thickness from about 2 nm to about 7 nm.
14. (Original) The method of Claim 13 where said first metal layer comprises Ta, Ti, W, Pt, Co, Ni, or combinations thereof.
- 15-16. (Cancelled)

17. (Currently amended) The method of Claim 1 wherein said first vertical silicide thickness is from about 5 nm to about 12 nm.
18. (Previously presented) The method of Claim 1 wherein said first silicide regions is formed in said substrate having a channel region beneath said gate region, where the distance between said first silicide regions and said channel region is from about 2 nm to about 15 nm.
19. (Previously presented) The method of Claim 1 wherein said first silicide regions is formed in said substrate having a channel region beneath said gate region, where the distance between said first silicide regions and said channel region is from about 3 nm to about 10 nm.
- 20-33. (Cancelled)